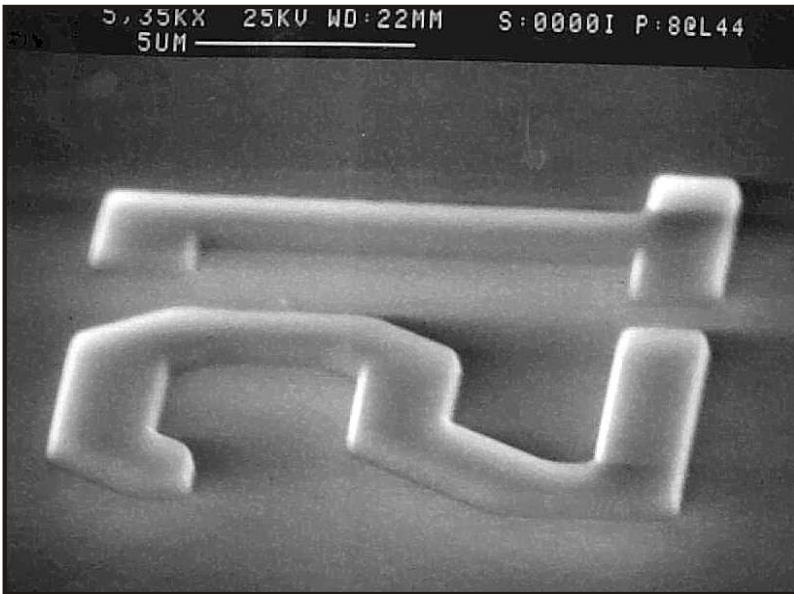


# Plasmalab Data

## Copper Etching for Failure Analysis



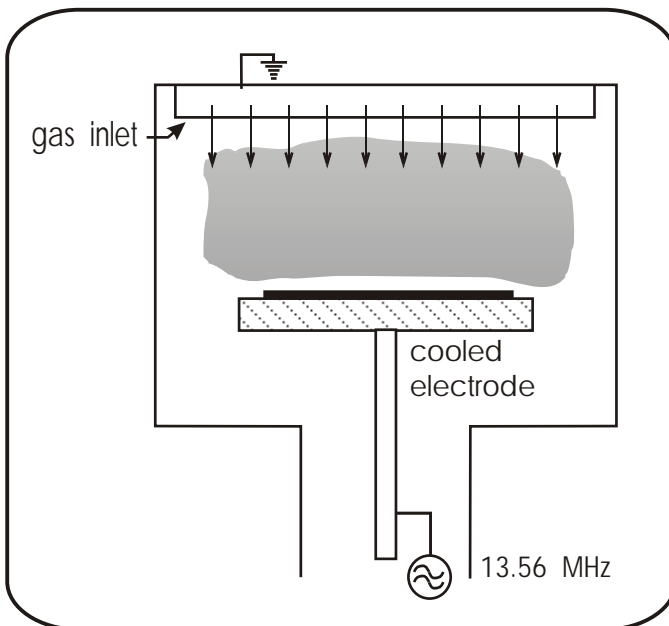
residue free copper etch



*Plasmalab System 100*

*Plasmalab System 133*

*Plasmalab 80 Plus*



**Equipment:**

- Plasmalab 80 Plus*
- Plasmalab System 100/ 133*
- (configured for Cu RIE)*

**Technology:**

- Parallel Plate Reactor
- Shower Head Gas inlet
- Chlorine based process

**Results:**

- rate : 300 nm/min (chip)
- uniformity:  $\pm 5\%$  (200 mm wafer)
- residue free etch
- selectivity to SiO<sub>2</sub>  $\geq 10 : 1$